Anemometer Anemometer

ROCHESTER INSTITUTE OF TECHNOLOGY MICROELECTRONIC ENGINEERING

Anemometer

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Page 1

3-13-2013 anemometer_lab.ppt



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Page 2



SINGLE WIRE ANEMOMETER

A single heater/sensor element is placed in the flow. The amount of power supplied to keep the temperature constant is proportional to flow. At zero flow a given amount of power Po will heat the resistor to temperature To. With non zero flow more power Pf is needed to keep the resistor at To.



THEORY

A resistor is heated and placed in fluid flow. Flow causes the temperature of the resistor to change and the temperature change causes a change in mobility that causes a change in the value of the resistance. The change in resistance is related to the velocity of the air flow, temperature of the sensor, temperature of the fluid, the specific heat of the fluid and the physical parameters of the resistor and the air flow chamber.

> Units of flow: sccm = standard cubic cm per min. Slm = standard liter per min.



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Page 4



THEORY

The resistance of the wire used will depend on its temperature according to the equation:

$$R_{w} = R_{0} [1 + \alpha (T_{w} - T_{0})]$$

The heat transfer coefficient, h, can be calculated according to King's law:

$$h = a + bv_f^n$$

Where a, b, and n are calibration coefficients. A value of 0.45 is commonly used for *n* in hot-wire anemometers. The value of *a* can be calculated by taking measurements with no fluid flow, and *b* can be found by using the recorded value of *a* at a known \widehat{H} flow rate.

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CALCULATION OF RESISTANCE

To use this spreadsheed change the values in the white boxes. The rest of the sheet is protected and should not be changed unless you are sure of the consequences. The calculated results are shown in the purple boxes. Calculation of Mobility of Single Crystal Silicon CONSTANTS VARIABLES CHOICES Tn = T/300 1.00 Temp= 3000 *K n-type 0 Concentration from Dose / thickness, N = Dose/t = $1.33E+18$ cm-3 p-type 1 Kamins, Muller and Chan; 3rd Ed., 2003, pg 33 mobility = $\mu = 131$ cm2/(V-sec) Calculation of Resistance L ength is the drawn length Length, L = 1000 µm Width is the drawn width Width, W = 2000 µm Thickness is known if poly, or Xj from Diffusion.XLS Thickness, t = 1.5 µm Implanter setting if doped by ion implant or from Diffusion.XLS Thickness = $2.00E+14$ /cm2 Poly ? 0 Yes=1, No =0 Average Doping = Dose/Thickness = $1.33E+18$ atoms/cm3 Mobility, $\mu = 131$ cm2/·sec $q = 1.6e-19$ coulomb / ion Rhos = sheet resistance = $1/(q \mu Dose) = 239$ ohms/sq Rho = bulk resistivity = 2.59 ohms/sq Rho = bulk resistivity = 2.59 ohms/sq Rho = bulk resistivity = 2.59 ohms/sq		M LENGTH, WIDTH, THICKNESS AND IMPLANT DOSE
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FLOW CALIBRATION

Dr. Pearson calibrated the airflow gauge on the bench by finding the amount of time it took to displace 2L of water in an upside down beaker. Manufacturers data sheet for Sapphire Ball gives 28.6 SLM full scale (marked as 150 on the gauge)





ANEMOMETER MEASUREMENTS

Calculate the current needed to generate ~1 watt in the poly resistor. The poly resistor is self heating and will reach some temperature with no gas flow. The resistance will change if gas flows over the resistor. To measure the response use the simple circuit shown.



PACKAGE GAS FLOW SENSOR



TEST SET UP FOR GAS FLOW SENSOR





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Page 18

RESULTS FROM PACKAGED SENSOR



STEP RESPONSE











